



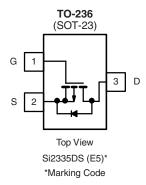
P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 12	0.051 at V _{GS} = - 4.5 V	- 4.0		
	0.070 at V _{GS} = - 2.5 V	- 3.5		
	0.106 at V _{GS} = - 1.8 V	- 3.0		

FEATURES

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFETs: 1.8 V Rated





Ordering Information: Si2335DS-T1-E3 (Lead (Pb)-free)

Si2335DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	Γ _A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Opation	T _A = 25 °C	I _D	- 4.0	- 3.2	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		- 3.3	- 2.6	
Pulsed Drain Current		I _{DM}	- 15		Α
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 1.6		
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	- P _D	1.25	0.75	W
	T _A = 70 °C		0.8	0.48	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lunation ta Analaianta	t ≤ 5 s	- R _{thJA}	75	100	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

Notes:

a. Surface mounted on 1" x 1" FR4 board.
b. Pulse width limited by maximum junction temperature.

Si2335DS

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SPECIFICATIONS $T_J = 25$	°C, unless	otherwise noted					
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, } I_D = -10 \mu\text{A}$				٧	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 9.6 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	μΑ	
0.01.0.10.10	1	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	- 6			Α	
		V _{GS} = - 4.5 V, I _D = - 4.0 A		0.042	0.051		
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -3.5 \text{ A}$		0.058	0.070	Ω	
		V _{GS} = - 1.8 V, I _D = - 2.0 A		0.082	0.106	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.0 A		7		S	
Diode Forward Voltage	V _{SD}	I _S = - 1.6 A, V _{GS} = 0 V			- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			9	15		
Gate-Source Charge	Q_{gs}	V_{DS} = - 6 V, V_{GS} = - 4.5 V, $I_D \cong$ - 4.0 A		1.9		nC	
Gate-Drain Charge	Q_{gd}			1.5			
Input Capacitance	C _{iss}			1225			
Output Capacitance	C _{oss}	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		260		pF	
Reverse Transfer Capacitance	C _{rss}			130			
Switching ^c							
Turn-On Time	t _{d(on)}			13.0	20		
Turr-On Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		15	25	ns	
Turn-Off Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{-}\ \text{1.0 A},\ \text{V}_\text{GEN}=\text{-}\ \text{4.5 V},\ \text{R}_\text{G}=\text{6}\ \Omega$		50	70	113	
Turri-Oir Tiffie	t _f			19	35		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

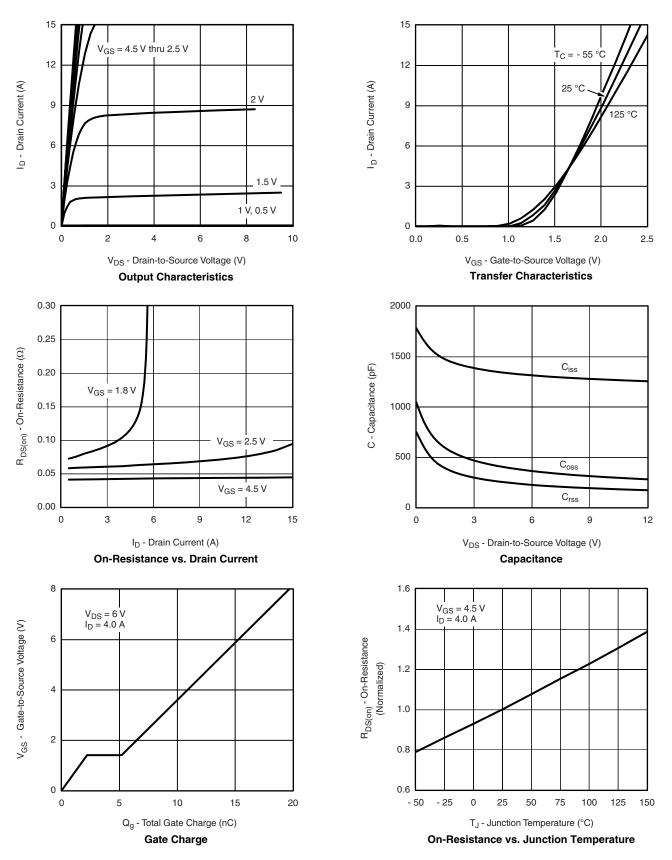
a. Pulse test: PW ≤ 300 μs, duty cycle ≤ 2 %.
b. For design aid only, not subject to production testing.
c. Switching time is essentially independent of operating temperature.







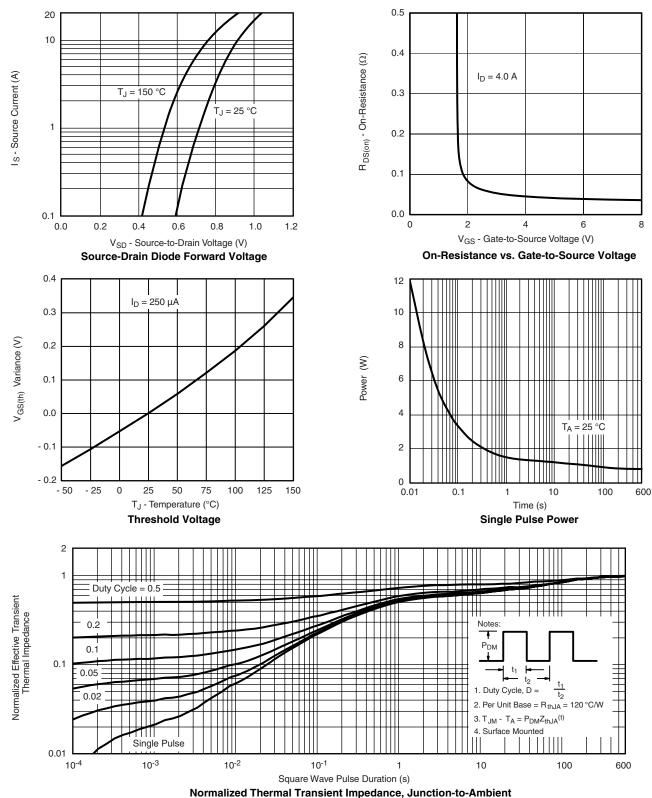
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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